Ordering number : EN5868

Red Laser Diode

DL-3149-055

Index Guided AlGaInP Laser Diode

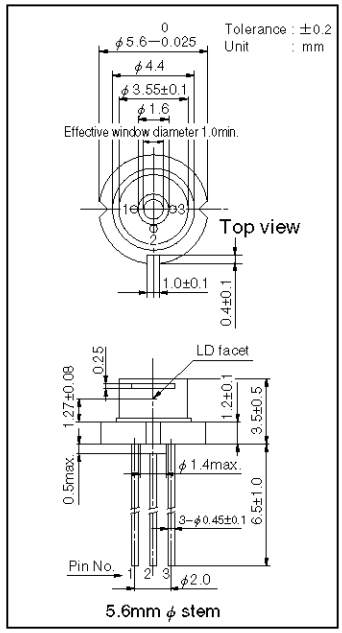
Overview

DL-3149-055 is 670 nm (Typ.) index guided AlGaInP laser diode with low threshold current. The low threshold current and short wavelength are achieved by the use of a strained multiple quantum well active layer. DL-3149-055 is suitable for applications such as bar-code scanners, laser pointers and other optical information systems.

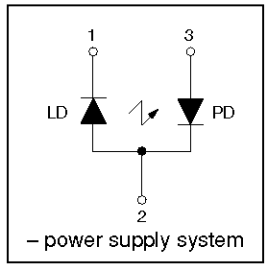
Features

- Short wavelength : 670 nm (Typ.)
- Output power : 5 mW CW
- Low threshold current : Ith = 35mA (Typ.)
- Small package : 5.6 mm ϕ

Package Dimensions



Electrical Connection



Absolute Maximum Ratings at Tc=25℃

Parameter		Symbol	Ratings	Unit
Light Output		Po	5	mW
Reverse Voltage	Laser	VR	2	V
	PIN		30	
Operating Temperature		Topr	–10 to +50	℃
Storage Temperature		Tstg	–40 to +85	℃

Electrical and Optical Characteristics at Tc=25℃

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Threshold Current		Ith	CW	–	35	60	mA
Operating Current		Iop	Po=5mW	–	45	70	mA
Operating Voltage		Vop	Po=5mW	–	2.3	2.6	V
Lasing Wavelength		λp	Po=5mW	660	670	680	nm
Beam Divergence ※)	Perpendicular	θ⊥	Po=5mW	25	33	40	deg.
	Parallel	θ//	Po=5mW	6	8	10	deg.
Off Axis Angle	Perpendicular	Δθ⊥	–	–	–	±2	deg.
	Parallel	Δθ//	–	–	–	±2	deg.
Differential Efficiency		dPo/dIop	–	0.15	0.3	–	mW/mA
Monitoring Output Current		Im	Po=5mW	0.4	1.2	2.0	mA
Astigmatism		As	Po=5mW	–	10	–	μm

※) Full angle at half maximum note : The above product specifications are subject to change without notice.

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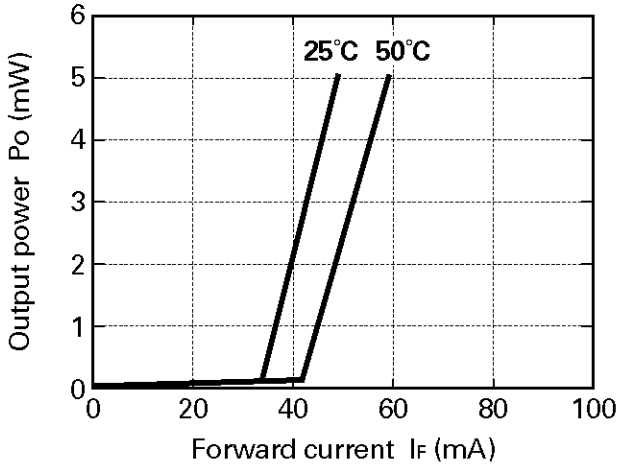
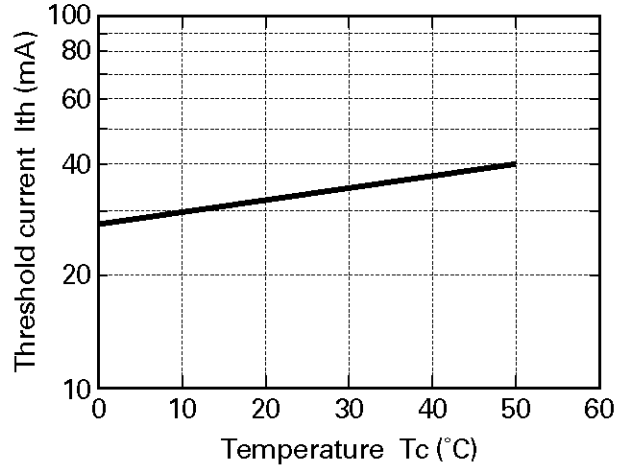
Characteristics

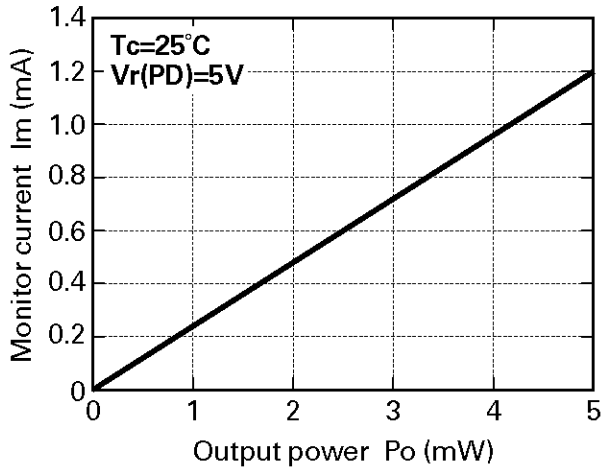
Output power vs. Forward current



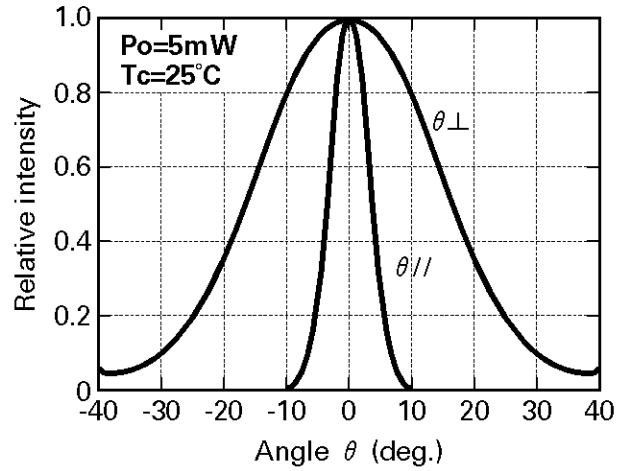
Threshold current vs. Temperature



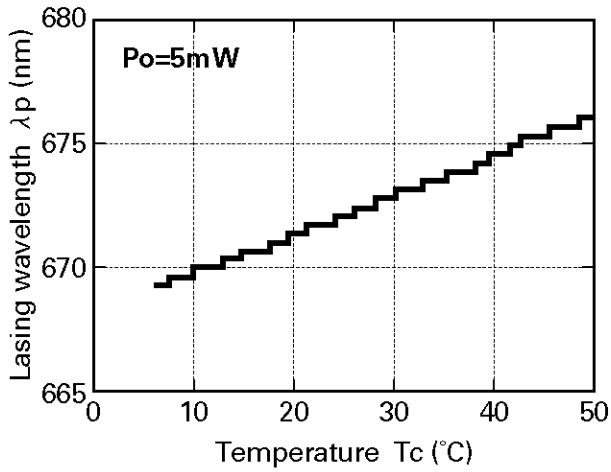
Monitor current vs. Output power



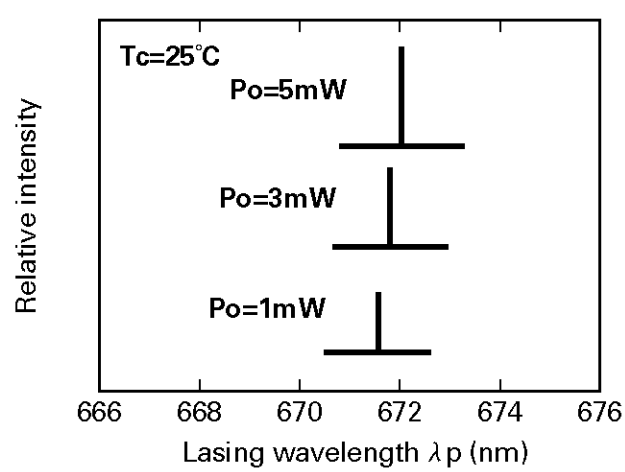
Beam divergence



Lasing wavelength vs. Temperature



Output power vs. Lasing wavelength



⚠ CAUTION

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Precautionary instructions in handling gallium arsenic products

Special precautions must be taken in handling this product because it contains, gallium arsenic, which is designated as a toxic substance by law. Be sure to adhere strictly to all applicable laws and regulations enacted for this substance, particularly when it comes to disposal.

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